

## Polishing surface layer of LiYF<sub>4</sub> single crystal

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### Abstract

By using methods of optical microscopy, microhardness and fast electrons diffraction in reflection mode it was determined that after mechanical polishing the depth of distorting layer is about 30  $\mu\text{m}$ . Optimal results for layer etching were obtained by using KOH at 60°. The distortionless surface at LiYF<sub>4</sub> single crystal was produced by mechanical polishing with chemical and ion-beam etching.

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